Test Booklet Code & Serial No.

प्रश्नपत्रिका कोड व क्रमांक

Paper-II **ELECTRONIC SCIENCE**

\mathbf{C}		

Signature and Name of Invigilator	Seat No.						
1. (Signature)	(In	i figi	ıres	as in	ı Adr	nit (Card)
(Name)	Seat No						
2. (Signature)		(In	word	ls)			
(Name)	OMR Sheet No.						
JUN - 38220	(To be	fille	d by	the (Cand	lidat	e)
Time Allowed: 2 Hours]		[M	axir	num	ı Ma	rks	: 200

Number of Pages in this Booklet: 32

Instructions for the Candidates

- Write your Seat No. and OMR Sheet No. in the space provided 1. on the top of this page.
- This paper consists of 100 objective type questions. Each question will carry two marks. All questions of Paper II will be compulsory. 2.
- 3. At the commencement of examination, the question booklet will be given to the student. In the first 5 minutes, you are requested to open the booklet and compulsorily examine it as follows
 - To have access to the Question Booklet, tear off the paper seal on the edge of this cover page. Do not accept a booklet without sticker-seal or open booklet.
 - (ii) Tally the number of pages and number of questions in the booklet with the information printed on the cover page. Faulty booklets due to missing pages/questions or questions repeated or not in serial order or any other discrepancy should not be accepted and correct booklet should be obtained from the invigilator within the period of 5 minutes. Afterwards, neither the Question Booklet will be replaced nor any extra time will be given. The same may please be noted.
 - After this verification is over, the OMR Sheet Number should be entered on this Test Booklet.
- 4. Each question has four alternative responses marked (A), (B), (C) and (D). You have to darken the circle as indicated below on the correct response against each item.

Example: where (C) is the correct response.









(D)

- Your responses to the items are to be indicated in the \mathbf{OMR} 5. Sheet given inside the Booklet only. If you mark at any place other than in the circle in the OMR Sheet, it will not be evaluated.
- Read instructions given inside carefully. 6.
- Rough Work is to be done at the end of this booklet.
- If you write your Name, Seat Number, Phone Number or put any mark on any part of the OMR Sheet, except for the space allotted for the relevant entries, which may disclose your identity, or use abusive language or employ any other unfair means, you will render yourself liable to disqualification.
- You have to return original OMR Sheet to the invigilator at the $\,$ 9. end of the examination compulsorily and must not carry it with you outside the Examination Hall. You are, however, allowed to carry the Test Booklet and duplicate copy of OMR Sheet on conclusion of examination.
- Use only Blue/Black Ball point pen. 10.
- Use of any calculator or log table, etc., is prohibited. 11.
- 12. There is no negative marking for incorrect answers.

Number of Questions in this Booklet: 100 विद्यार्थ्यांसाठी महत्त्वाच्या सुचना

- परिक्षार्थींनी आपला आसन क्रमांक या पृष्ठावरील वरच्या कोप-यात लिहावा. 1. तसेच आपणांस दिलेल्या उत्तरपत्रिकेचा क्रमांक त्याखाली लिहावा.
- सदर प्रश्नपत्रिकेत 100 बहुपर्यायी प्रश्न आहेत. प्रत्येक प्रश्नास दोन गुण 2. आहेत. या प्रश्नपत्रिकेतील **सर्व** प्रश्न सोडविणे अनिवार्य आहे.
- परीक्षा सरू झाल्यावर विद्यार्थ्याला प्रश्नपत्रिका दिली जाईल. सरुवातीच्या 5 मिनीटांमध्ये आपण सदर प्रश्नपत्रिका उघड्न खालील बाबी अवश्य तपासून
 - प्रश्नपत्रिका उघडण्यासाठी प्रश्नपत्रिकेवर लावलेले सील उघडावे. सील नसलेली किंवा सील उघडलेली प्रश्नपत्रिका स्विकारू नये.
 - पहिल्या पृष्ठावर नमुद केल्याप्रमाणे प्रश्नपत्रिकेची एकृण पृष्ठे (ii)तसेच प्रश्नपत्रिकेतील एकण प्रश्नांची संख्या पडताळून पहावी. पष्ठे कमी असलेली/कमी प्रश्न असलेली/प्रश्नांचा चकीचा क्रम असलेली किंवा इतर त्रुटी असलेली सदोष प्रश्नपत्रिका सुरुवातीच्या 5 मिनिटातच पर्यवेक्षकाला परत देऊन दुसरी प्रश्नपत्रिका मागवून घ्यावी. त्यानंतर प्रश्नपत्रिका बदलून मिळणार नाही तसेच वेळही वाढवून मिळणार नाही याची कृपयाँ विद्यार्थ्यांनी नोंद घ्यावी.
 - वरीलप्रमाणे सर्व पडताळून पाहिल्यानंतरच प्रश्नपत्रिकेवर ओ.एम.आर. उत्तरपत्रिकेचा नंबर लिहावा.
- प्रत्येक प्रश्नासाठी (A), (B), (C) आणि (D) अशी चार विकल्प उत्तरे दिली आहेत. त्यातील योग्य उत्तराचा रकाना खाली दर्शविल्याप्रमाणे ठळकपणे काळा/निळा करावा.

उदा. : जर (C) हे योग्य उत्तर असेल तर









- या प्रश्नपत्रिकेतील प्रश्नांची उत्तरे ओ.एम.आर. उत्तरपत्रिकेतच दर्शवावीत. इतर ठिकाणी लिहिलेली उत्तरे तपासली जाणार नाहीत.
- 6. आत दिलेल्या सूचना काळजीपूर्वक वाचाव्यात.

5.

- प्रश्नपत्रिकेच्या शेवटी जोडलेल्या कोऱ्या पानावरच कच्चे काम करावे. 7.
- जर आपण ओ.एम.आर. वर नमुद केलेल्या ठिकाणा व्यतिरीक्त इतर कोठेही नाव, आसन क्रमांक, फोन नंबर किंवा ओळख पटेल अशी कोणतीही खुण केलेली आढळून आल्यास अथवा असभ्य भाषेचा वापर किंवा इतर गैरमार्गांचा अवलंब केल्यास विद्यार्थ्याला परीक्षेस अपात्र ठरविण्यात येईल.
- परीक्षा संपल्यानंतर विद्यार्थ्याने मूळ ओ.एम.आर. उत्तरपत्रिका पर्यवेक्षकांकडे 9. परत करणे आवश्यक आहे. तथापि, प्रश्नपत्रिका व ओ.एम.आर. उत्तरपत्रिकेची द्वितीय प्रत आपल्याबरोबर नेण्यास विद्यार्थ्यांना परवानगी आहे.
- फक्त निळ्या किंवा काळ्या बॉल पेनचाच वापर करावा. 10.
- कॅलक्युलेटर किंवा लॉग टेबल वापरण्यास परवानगी नाही. 11.
- चुकीच्या उत्तरासाठी गुण कपात केली जाणार नाही.

JUN - 38220/II—C

Electronic Science Paper II

	ne Allowed: 120 Minutes] te: This Paper contains Hundred (100) carrying Two (2) marks. Attempt		
1.	The maximum and the minimum siz	e of a	a segment in 8086 is:
	(A) 64 K, 16 bytes	(B)	32 K, 256 bytes
	(C) 16 K, 16 bytes	(D)	64 K, 256 bytes
2.	8051 has 8 bit data bus, but it can	gener	ate 16 bit addresses using:
	(A) IO/M	(B)	ALE
	(C) R/W	(D)	$\overline{\mathrm{EA}}$
3.	Which of the following represents inc	dexed	addressing?
	(A) MOVC A, @ + DPTR	(B)	AJMP addr.
	(C) SET B 07H	(D)	MOV A, 47H
4.	The alternate function of 8051 port	2 is :	
	(A) Input/output data $(D_0 - D_7)$		
	(B) Sending higher order address (A	. ₈ – A	A ₁₅)
	(C) Sending lower order address (A ₀	- A ₇	7)
	(D) Serial input/output		
5.	Bus arbitration, Bus Request and Bu	ıs Gr	ant are terms used in:
	(A) Serial communication	(B)	Memory map design
	(C) Direct memory access	(D)	Address/Data Multiplexing

6.	The timer 0 of 8051 with 1 MHz clock ca	n generate maximum delay of
	with resolution	
	(A) 64 ms, 1 μs	(B) 64 µs, 1 ms
	(C) 32 µs, 100 ms	(D) 256 ms, 1 μs
7.	When two BCD numbers are added, the	answer is a non-BCD number. To convert
	it in BCD form the instruction used	is:
	(A) SUBB A, # data	(B) XCH A, Rn
	(C) ADD A, Rn	(D) DA A
8.	Arrange the sequence of 8086 interrupts	s as per the priority assigned, from lowest
	to highest:	
	(1) Single step	
	(2) INTR	
	(3) NMI	
	(4) Divide error, Int n , INTO	
	(A) (2) (3) (4) (1)	
	(B) (1) (2) (3) (4)	
	(C) (3) (2) (1) (4)	
	(D) (1) (3) (2) (4)	

9. Match List I with List II:

List I

(Instruction)

(a) DJNZ, R3, 100p

- (b) ADD R4
- (c) LCALL 2020
- (d) SWAP

Codes:

- (a) (b) (c) (d)
- (A) (4) (2) (3) (1)
- (B) (4) (3) (2) (1)
- (C) (4) (1) (2) (3)
- (D) (3) (4) (1) (2)

10. Assertion (A):

High data rate can be handled by reducing the interrupt overheads.

Reason (R):

DMA is fast data transfer process.

- (A) Both (A) and (R) are true and (R) is correct explanation of (A)
- (B) Both (A) and (R) are true but (R) is not correct explanation of (A)

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- (C) (A) is true but (R) is false
- (D) (A) is false but (R) is true

List II

(Addressing Mode)

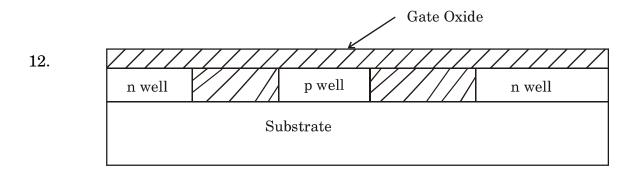
- (1) Implied
- (2) Direct
- (3) Register
- (4) Relative

- 11. cannot be fabricated on an IC.
 - (A) Transistors

(B) Diodes

(C) Resistors

(D) Large inductors and transformers



Gate oxide layer consists of:

- (A) SiO₂ layer, overlaid with a few layers of an oxynitrided oxide
- (B) Only SiO₂ layer
- (C) SiO_2 layer with polysilicon layer
- (D) SiO_2 layer and stack of epitaxial layer of polysilicon
- 13. X-ray diffraction patterns are used for studying crystal structure of solids because :
 - (A) X-rays have high energy and hence they can penetrate through solids
 - (B) X-rays are electromagnetic radiation, therefore they do not interact with matter
 - (C) X-ray wavelengths are comparable to inter-atomic distance
 - (D) High frequency of X-rays allows quick analysis

14. In the CMOS stick diagrams the n and p transistors are separated by :

(A) Thick black line

(B) Dotted blue line

(C) Thick yellow line

(D) Dotted brown line

15. For CMOS circuits which of the following is true?

- (A) There is low power consumption during high speed switching
- (B) There is high power consumption in static condition
- (C) There is negligible power consumption during dynamic condition
- (D) The dynamic power consumption increases with increasing frequency of operation

Which equation is *correct* for a digital gate with symbols carrying usual meaning?

(A)
$$V_{NL} = V_{1L(Max)} + V_{0L(Max)}$$

(A)
$$V_{NL} = V_{1L(Max)} + V_{0L(Max)}$$
 (B) $V_{NH} = V_{0H(Min)} + V_{1H(Min)}$

(D)
$$V_{NH} = V_{0H(Min)} - V_{1H(Min)}$$

17. Assertion (A):

Shallow Trench Isolation (STI) prevents electrical current leakage between adjacent semiconductor devices.

Reason (R):

STI process involves etching a pattern of trenches in silicon and filling them with insulating SiO₂.

- (A) Both (A) and (R) are true and (R) is the correct explanation of (A)
- (B) Both (A) and (R) are true but (R) is not the correct explanation of (A)
- (C) (A) is true but (R) is false
- (D) (A) and (R) both are false

18. Match List I with List II:

List I

- (a) ion implantation
- (b) etching
- (c) oxidation
- (d) metallization

Codes:

- (a) (b) (c) (d)
- (A) (1) (2) (3) (4)
- (B) (4) (3) (2) (1)
- (C) (4) (2) (1) (3)
- (D) (2) (3) (4) (1)

19. 'Register Transfer Level' means:

- (A) A structure that deals with only behavioural constructs
- (B) A structure that combines both behavioural and data flow constructs and can be acceptable by logic synthesis tools
- (C) A structure that deals with only data flow constructs
- (D) A structure that defines transfer of register from one region to the other

List II

- (1) interconnect between devices
- (2) insulating dielectric layer
- (3) removal of unwanted material
- (4) low temperature impurity insertion

20.	IIR	filters are:		
	(A)	Recursive where present output de output samples only	epend	ls on present and past inputs and
	(B)	Non-recursive where present outp	ut de	epends on present and past input
	(C)	Recursive where present output deponly	ends	on present and past input samples
	(D)	Non-recursive where present output and output samples only	ut de	pends on present and past inputs
21.	ECO	G is recorded with the help of:		
	(A)	Non-contact probes	(B)	Surface metal electrodes
	(C)	Penetrating metal electrodes	(D)	Optical electrodes
22.	The	stub length on single stub match	ing	cancels :
	(A)	Susceptance	(B)	Permeability
	(C)	Conductance	(D)	Inductance
23.	The	principle mode of propagation in	co-ax	ial line is mode.
	(A)	TE	(B)	TM
	(C)	TEM	(D)	TE_{11}
24.	The	distance around one cycle of Smi	th cl	nart is :
	(A)	λ	(B)	$\lambda/4$
	(C)	$\lambda /2$	(D)	λ/8

25.	The value of directivity of isotropic	antenna is:
	(A) 1	(B) 0
	(C) ∞	(D) 0.5
26.	A transmission line has a VSWR of	2, the reflection coefficient is equal to:
	(A) 1/3	(B) 0
	(C) 1/4	(D) 1/2
27.	In a microwave system, wave guides	has the advantage of:
	(A) Positive phase shift	
	(B) High power handing capability a	and low loss
	(C) Thin dielectric substrate	
	(D) Coupling with co-axial wave gui	des
28.	Arrange the following S-parameters	of E-plane in increasing order of value :
	(a) S12	(b) S13
	(c) S23	(d) S33
	(A) (d) , (c) , (a) , (b)	
	(B) (d) , (a) , (b) , (c)	
	(C) (a) , (d) , (c) , (b)	
	(D) (c) , (d) , (a) , (b)	

29. Match the following List I and List II:

List I

- (a) Directivity (D)
- (b) Antenna Efficiency (n)
- (c) Fraunhofer Region (R)
- (d) The effective area of an antenna (Ae)

List II

$$(1) \quad \frac{\lambda^2 G}{4\pi}$$

(2) $\geq 2D^2 / \lambda$

 $(3) \quad \frac{\text{Radiated Power}}{\text{Total Input Power}}$

of Single Antenna
Radiation Intensity of an
Isotropic Antenna

Max Radiation Intensity

Codes:

- (a) (b) (c) (d)
- (A) (2) (3) (4) (1)
- (B) (1) (2) (4) (3)
- (C) (4) (3) (2) (1)
- (D) (2) (3) (1) (4)
- 30. Delay line cancellor in RADAR:
 - (A) Improves SNR
 - (B) Rejects stationary clutter at zero frequency

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- (C) Corresponds to amplifier echo
- (D) Is frequency domain filter

31.	Protocol used to link devices in IOT	is :	
	(A) TCP/IP	(B)	I^2C
	(C) SPI	(D)	UDP
32.	Cyclic redundancy check and hamming	g cod	e works on data of and
	respectively.		
	(A) 8-bit size, any size	(B)	fixed size, any size
	(C) any size, fixed size	(D)	2-bit size, any size
33.	In source coding theorem if, discrete i	nemo	oryless source of entropy H(S) and
	average code-word length \bar{L} , the source	e codi	ing theorem has following
	relation.		
	$(A) \overline{L} \leq H(S)$	(B)	$\bar{L} \geq H(S)$
	$(C) \overline{L} \geq log H(S)$	(D)	$\overline{L} \leq logH(S)$
34.	Cloud computing corresponds to :		
	(A) Analysis of metrological data		
	(B) Agglomeration of computing and	stora	age resources
	(C) Localised high performance comp	uting	;
	(D) Mobile data management		
35.	In the vestigial sideband amplitude mod	ulatio	on (AM-VSB), the transmitted signal
	has a bandwidth of, where B	is b	andwidth of original analog signal.
	(A) $B - \Delta$	(B)	$B + \Delta$
	(C) B $\pm \Delta$	(D)	$B \pm 2\Delta$

36.	Diff	eren	tial p	ulse	coded modula	tion exp	loits	the between samples to
	•••••	•••••	. enco	ding	rate.			
	(A)	auto	corre	latio	n, decrease		(B)	correlation, increase
	(C)	auto	corre	latio	n, increase		(D)	correlation, decrease
37.	The	size	of I	Pv6	address is :			
	(A)	32 l	oit				(B)	64 bit
	(C)	128	bit				(D)	256 bit
38.	Mat	tch I	ist I	with	n List II and	d select	the	correct answer using codes given
	belo	w:						
		List	t I					List II
	(a)	Erro	or sig	nal			(1)	Modulated signal
	(b)	Con	trol s	signa	1		(2)	Phase detector
	(c)	Out	put s	ignal			(3)	Loop filter
	(d)	Inpu	ıt sig	nal			(4)	Voltage controlled oscillator
	Cod	des :	:					
		(a)	(<i>b</i>)	(c)	(<i>d</i>)			
	(A)	(2)	(4)	(3)	(1)			
	(B)	(4)	(3)	(1)	(2)			
	(C)	(2)	(3)	(4)	(1)			
	(D)	(4)	(1)	(3)	(2)			

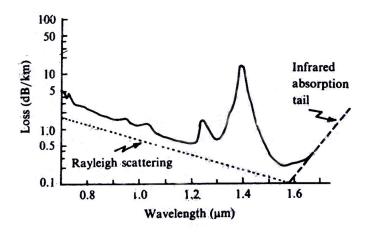
39.	The main difference between Amplitude modulation and Frequency modulation
	is that:
	(a) Carrier frequency is higher than base band frequency
	(b) Frequency modulation has limited bandwidth
	(c) Frequency modulation has unlimited bandwidth
	(d) Intermediate frequency stage is found in frequency demodulator circuit
	(A) (a) and (c) (B) (c) and (d)
	(C) (b) and (d) (D) (c) only
40.	A spectrum analyser is an instrument used for:
	(A) Visualising time variation of a waveform
	(B) Identifying dominant frequencies and harmonics
	(C) Introducing noise floor
	(D) Determination of impedance of an element
41.	When checking a good SCR with an ohmmeter it will:
	(A) Show low resistance with positive on anode and negative on cathode and high resistance when reversed
	(B) Show low resistance in both directions
	(C) Show high resistance in both directions
	(D) Show high resistance with positive on anode and negative on cathode, and low resistance when reversed
42.	UJT is often used in power controlling circuits because of:
	(A) Excellent triggering properties
	(B) High power dissipation

(D) Capable of supplying high current for triggering

(C) Large breakdown voltage

43.	Wei	ght o	of SM	PS ba	ased 12 volts adopter	s mucl	h lower as compared to conventional
	ado	pter	becau	use S	SMPS uses :		
	(A)	Feri	rite ti	ransf	ormers	(B)	Power MOSFETS
	(C)	Rect	tifiers	s in t	the first stage	(D)	High frequency step-down
44.	The	adv	antag	ge of	on-line UPS over	off-line	e UPS is that:
	(A)	Give	e true	e sin	e wave		
	(B)	The	re is	no p	ohase change of out	put d	uring mains failure
	(C)	The	y can	n pro	vide high power ar	d lon	g duration
	(D)	Effic	ciency	y of	conversion is very	high	
45.	Mat	tch t	he fo	llowi	ng for on-state resi	stance	e for the device in milliohms :
		Set	Ι				Set II
	(a)	Dioc	de			(1)	0.25
	(b)	ВЈТ	•			(2)	0.16
	(c)	SCF	2			(3)	3.5
	(d)	Tria	ıc			(4)	4.0
	Cod	des :	:				
		(a)	(<i>b</i>)	(c)	(d)		
	(A)	(2)	(4)	(1)	(3)		
	(B)	(3)	(4)	(1)	(2)		
	(C)	(4)	(2)	(3)	(1)		
	(D)	(1)	(2)	(4)	(3)		

Directions 46 to 49:



The shifting of the operating wavelength to the 1.3 µm range has another important advantage. The corresponding loss is much smaller. Fig. above shows the loss spectrum for a typical optical fibre and as can be seen the losses at $\lambda_0 \sim 1.3$ µm are ~ 1 dB/km which is smaller by a factor of about 3 when compared with losses at $\lambda_0 \sim 0.8$ µm. Optical communication systems around 1981 used graded index multimode fibres with 1.3 µm sources; typical sources used were InGaAsP/InP LEDs ($\Delta\lambda_0 \approx 25$ nm) and laser diodes ($\Delta\lambda_0 \approx 2$ nm) with Ge APDs as detectors. The losses in the fibres were ~ 1 dB/km. These systems are usually said to belong to second generation optical communication systems. In a typical operating system the repeater spacing was 30 km and the bit rate was ~ 45 Mbit/s. Thus, in comparison to first generation systems, the repeater spacing was increased by a factor of about 2.5 which was primarily due to the decrease in pulse dispersion as well as in the losses in optical fibres.

As shown above by operating at 1.3 µm wavelength, material dispersion has become extremely small and therefore the information-carrying capacity is limited by intermodal dispersion. This intermodal dispersion can be totally eliminated by using single mode fibres where only one guided mode is possible.

This will be discussed in the following section.

	17		P.T.O.
	(C) 1×10^{-6} m	(D) 1×10 ⁻⁹ m	
	(A) 1×10^6 m	(B) 1×10^{-3} m	
50.	The size of functional elements in MI	EMS is of the order of:	
	(C) 0.14 µm	(D) 0.15 µm	
	(A) $0.85~\mu m$	$(B) 0.13 \ \mu m$	
	for a silica fiber :		
49.	Intramodal dispersion is not a limiting	g factor in the following spectral	region
	(D) to reduce the disportion problems	at 1300 nm	
	(C) to make use high quality laser d	iodes	
	(B) to obtain low attenuation at 1300) nm	
	(A) to increase mechanical strength of	of fiber for 1300 nm operation	
	1550 nm to 1300 nm is:		
48.	The primary reason for shifting	characteristic of optical fib	er at
	(D) impurities have no effect in trans	smission	
	(C) components are easily available		
	(B) bandwidth is highest		
	(A) attenuation is lowest		
	the:		
47.	Importance of 1.3 µm range in optical	communication arises to the fac	t that
	(C) 1.3 µm	(D) 0.8 µm	
	(A) 25 nm	(B) 2 nm	
46.	Emission wavelength of InGaAsP/InP	device is:	

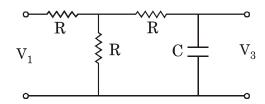
51.	Force exerted by magnetic field in H	all ef	fect transducer is:
	(A) Lorentz force	(B)	Hall effect
	(C) Magnetic force	(D)	Electric force
52.	The bridge balance equation can be	writte	en in :
	(A) Impedance form	(B)	Resistance form
	(C) Conductance form	(D)	Admittance form
53.	Following is the most accurate temper	eratur	re transducer :
	(A) Thermistor	(B)	Thermocouple
	(C) Radiation thermometer	(D)	Bimetal strips
54.	Lissajous figure corresponding to pha	se di	fference of $3\pi/4$ is :
	(A)	(B)	
	(C)	(D)	
55.	The best suited flow-meter to handle	corre	osive liquids is :
	(A) Displacement flow-meter	(B)	Piston type flow-meter
	(C) Turbine flow-meter	(D)	Magnetic flow-meter
56.	Characteristic equation in a control s	ysten	n is a relation formed by:
	(A) Equating to zero the denominator	of tra	ansfer function
	(B) Equating to zero the numerator	of tra	ansfer function
	(C) Equating numerator to denomina	tor o	f transfer function

(D) Equation both numerator and denominator to zero of the transfer function

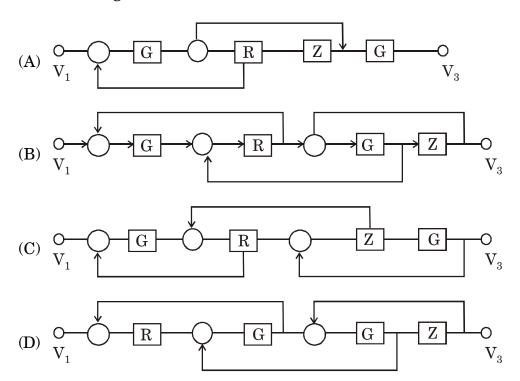
- 57. The frequency that would occur for two complex poles if the damping were equal to zero is called :
 - (A) Forced damping frequency
- (B) Critical damping frequency

(C) Natural frequency

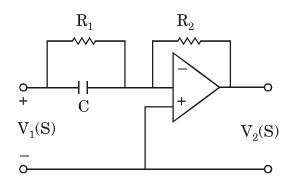
- (D) Conditional frequency
- 58. For the following ladder network:



its block diagram is:



59. The transfer function of the following differentiating circuit is:



(A)
$$- \left[\frac{R_2(R_1C_s + 1)}{R_1} \right]$$

(B)
$$-\left\lceil \frac{R_1(R_2C_s+1)}{R_2} \right\rceil$$

$$\text{(C)} \ \left\lceil \frac{R_1 R_2 (C_s + 1)}{R_1} \right\rceil$$

$$(D) \quad \left\lceil \frac{R_2(R_1C_s-1)}{R_1} \right\rceil$$

60. Assertion (A):

Many of the linear control system transfer functions do not have poles or zeroes in the right half s-plane.

Reason (R):

These are called minimum phase transfer functions.

- (A) Both (A) and (R) are true and (R) is correct explanation of (A)
- (B) Both (A) and (R) are true and (R) is not correct explanation of (A)
- (C) (A) is true, (R) is false
- (D) (A) is false, (R) is true

61.	Which of the following is <i>not</i> a semiconductor ?							
	(A) Galium Arsenide	(B)	Indium					
	(C) Germanium	(D)	Silicon					
62.	In the case of N-type semiconductor the	ener	gy required to detach fifth electron					
	from the donor atom is:							
	(A) 0.01 eV	(B)	0.05 eV					
	(C) 0.25 eV	(D)	0.70 eV					
63. P-side of a semiconductor diode is applied a potential of $0.5~\rm V$ wherea N-side is applied a potential of $-1.0~\rm V$. The diode shall :								
	(A) Conduct partially	(B)	Not conduct					
	(C) Conduct	(D)	Breakdown					
64.	throughout its volume. The semiconductor is N-type with $N_D=10^{19}/{\rm cm}^3$. It the excess electron concentration in the steady state is $\Delta_n=10^{15}/{\rm cm}^2$ and $\tau_p=10~{\rm \mu s}$ C minority carrier life time, then what is the generation rate due to irradiation?							
	(A) 10^{20} e-h pairs/cm ³ /s		10 ¹⁴ e-h pairs/cm ³ /s					
	(C) 10^{10} e-h pairs/cm ³ /s	(D)	10 ⁸ e-h pairs/cm ² /s					
65.	Compared to BJT, a JFET has:							
	(A) Lower input impedance							
	(B) Higher voltage gain							
	(C) Higher input impedance and high	h vol	tage gain					
	(D) Higher input impedance and low	volta	age gain					

66.	In a MOSFET devices, the N-channel type is better than the P-channel type						
	in the following respect:						
	(A) It has better noise immunity	(B) It is faster					
	(C) It is TTL compatible	(D) It has drive capability					
67.	7. Hydrofluoric acid is preferred in wet etching. Which of the following is/are cc						
	for Hydrofluoric acid (HF) ?						
	(1) HF does not attack ${ m SiO}_2$						
	(2) HF attacks SiO_2						
	(3) HF affects silicon substrate under	rneath					
	(4) HF does not affect silicon substrate underneath						
	(A) 1 and 2	(B) 2 and 3					
	(C) 2 and 4	(D) 1 and 3					
68.	68. In the case of degenerate P-type material which of the following is/a correct ?						
(1) Acceptor concentration is very high							
	(2) Donor concentration is very high						
	(3) The Fermi level lies in the valence band						
	(4) The Fermi level lies in the conduction band						
	(A) 1 only	(B) 2 only					
	(C) 2 and 4	(D) 1 and 3					

- 69. Which solution is used when the silicon water undergoes chemical-mechanical polishing ?
 - (A) a slurry of very fine ${\rm SiO}_2$ particles in basic KOH solution
 - (B) a slurry of very fine SiO₂ particles in a basic NaOH solution
 - (C) a slurry of very fine ${\rm SiO}_2$ solution only
 - (D) in a NaOH solution only
- 70. Match List I with List II:

List I

- (a) Si + O_2
- (b) Si + $2H_2O$
- (c) Ion implantation
- (d) Rapid thermal processing

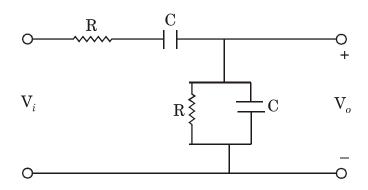
Codes:

- (a) (b) (c) (d)
- (A) (3) (1) (2) (4)
- (B) (1) (3) (4) (2)
- (C) (3) (1) (4) (2)
- (D) (1) (2) (4) (3)

List II

- (1) Wet oxidation
- (2) Operates for only few seconds at high temperatures
- (3) Dry oxidation
- (4) Projected range

71. The RC circuit shown in the following figure, is:



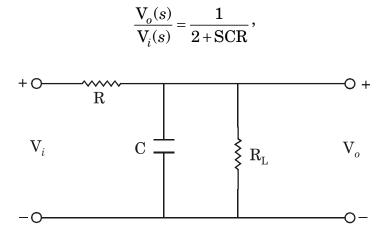
(A) a low pass filter

(B) a high pass filter

(C) a band pass filter

(D) a band reject filter

72. If the transfer function of the following network is



then the value the Load Resistor \boldsymbol{R}_{L} is :

(A) R/4

(B) R/2

(C) R

(D) 2R

	(B) Linearity (D) Non-linearity lian/second has a source impedance consisting H inductance. The load that will obtain the						
74. A source of angular frequency 1 rad	dian/second has a source impedance consisting						
of 1 Ω resistance in series with 1	H inductance. The load that will obtain the						
max power transfer is:							
(A) 1 Ω resistance							
(B) 1 Ω resistance in parallel wi	(B) 1 Ω resistance in parallel with 1 H inductance						
(C) 1 Ω resistance in series with	1 F capacitor						
(D) 1 Ω resistance in parallel wi	th 1 F capacitor						
75. A DC voltage source is connected	l across a series RLC circuit. Under steady						
state conditions, the applied DC	state conditions, the applied DC voltage drops entirely across the :						
(A) C only	(B) L only						
(C) R only	(D) R and L combinations						
76. Consider a DC voltage source V_S	Consider a DC voltage source V_{S} connected to a series RC circuit. When the						
steady state reaches, the ratio of t	steady state reaches, the ratio of the energy stored in the capacitor to the total						
energy supplied by the voltage s	energy supplied by the voltage source is equal to:						
(A) 0.322	(B) 0.632						
(C) 0.500	(D) 1.000						

77. Convolution of:

x(n) = (1, 2, 1) and $h(n) = \{1, 2, -1\}$

will be:

(A) $\{1, 4, 4, 1, -1\}$

(B) $\{1, 1, 4, 4, -1\}$

(C) {1, -1, 1, 4, 4}

- (D) {4, 4, 1, 1}
- 78. z-transform of $x(n n_0)$ is :
 - (A) $z^{-n_0} X(2)$

(B) $z^{+n_0} X(2)$

(C) X(z-20)

- (D) z^{-n} . X(2)
- 79. Image impedances of port 1 and port 2 of symmetrical two-port network is:
 - (A) Zero

(B) Infinite

(C) Equal

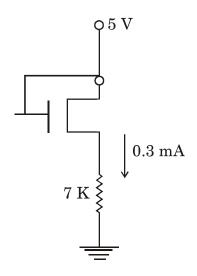
- (D) Not equal
- 80. Laplace transform of parabolic function is:
 - (A) 2/s

(B) $1/s^2$

(C) 1/s³

- (D) $2/s^3$
- 81. Which of the following does not adopt any feedback?
 - (A) Phase shift oscillator
 - (B) UJT relaxation oscillator
 - (C) Wein-Bridge oscillator
 - (D) Colpit's oscillator

82. Estimate V_{GS} in the following circuit :



(A) 1.5 V

(B) 4.9 V

(C) 3.5 V

- (D) 2.9 V
- 83. In LM 317 minimum value of voltage required between its input and output for proper functioning is:
 - (A) 3 V

(B) 1 V

(C) 5 V

- (D) 10 V
- 84. Gain bandwidth product of an amplifier after inclusion of negative feedback:
 - (A) Decreases

(B) Increases

(C) Remains constant

- (D) Becomes zero
- 85. Bridge rectifier is an alternative to:
 - (A) Full wave rectifier

(B) Half wave rectifier

(C) Voltage regulator

- (D) π -section filter
- 86. Which of the following holds good for a phase locked loop?
 - (A) Lock range < capture range
 - (B) Lock range > capture range
 - (C) VCO frequency > input frequency during lock
 - (D) VCO input voltage is zero during lock

87.			of the	e fol	lowing can be us	ed as a	a substitute for analog to digital	
	(A)	Fre	quen	cy to	voltage convertor	(B)	Astable multivibrator	
	(C)	Vol	tage	to fr	equency convertor	(D)	Voltage regulator	
88.	Starting from AC mains towards load, identify the <i>correct</i> sequence of building block of a regulated power supply :							
	(A)	(A) Rectifier, Regulator, Filter, Transformer						
	(B)	(B) Transformer, Filter, Regulator, Rectifier						
	(C)	(C) Transformer, Rectifier, Filter, Regulator						
	(D) Regulator, Transformer, Rectifier, Filter						er	
89.	Match the pairs between List I and List II:							
	List I						List II	
	(a)	Neg	gative	feed	lback	(1)	Comparator with controlled	
							hysteresis	
	(b) Bipolar junction transistor		(2)	Increased stability				
	(c)	Operational amplifier				(3)	Current controlled current amplifier	
	(d)	Sch	mitt	Trigg	ger	(4)	High open loop gain	
	Codes:							
		(a)	(<i>b</i>)	(c)	(d)			
	(A)	(2)	(3)	(1)	(4)			
	(B)	(3)	(1)	(2)	(4)			
	(C)	(2)	(3)	(4)	(1)			
	(D)	(1)	(2)	(3)	(4)			

90. Assertion (A):

Current gain of a Darlington pair is much higher compared to that of individual transistor.

Reason (R):

Input impedance is high due to negative feedback.

- (A) Both (A) and (R) are true and (R) is the correct explanation of (A)
- (B) Both (A) and (R) are true but (R) is not the correct explanation of (A)
- (C) (A) is true but (R) is false
- (D) (A) is false and (R) is true
- 91. A demultiplexer is called a data distributor because:
 - (A) The input is distributed to one of the outputs
 - (B) One of the inputs is selected for the output
 - (C) The output is distributed to one of the inputs
 - (D) The output is buffered
- - (A) 45 ns and 60 ns

(B) 60 ns and 15 ns

(C) 15 ns and 60 ns

- (D) 30 ns and 15 ns
- 93. The state diagram for a JKFF consists of :
 - (A) One state

(B) Two states

(C) Three states

(D) Four states

94.	The following HDL statement will implement:					
	assign $Y = (A \& \& S) \parallel (B \& \& S).$					
	(A) 4-bit Encoder	(B) 4-bit Decoder				
	(C) 2:1 Multiplexer	(D) 1:2 DEMUX				
95.	The minimum number of bits of ADC	required to monitor the temperature in				
	the range $0-100^{\circ}\mathrm{C}$ with resolution of	f 1°C and the corresponding output at				
	25°C will be:					
	(A) 8-bits and 0100 0000	(B) 6-bits and 110 000				
	(C) 12-bits and 0000 1010 1111	(D) 10-bits and 10001 01000				
96.	6. An amount of memory required to store a 256 gray shade monochrome image					
	with 512×512 resolution will be :					
	(A) 256 K bytes	(B) 512 K bytes				
	(C) 1 M bytes	(D) 64 K bytes				
97.	. In a data transmission system, the set of possible symbols is:					
$\{lower-case\ alphabet\}\ \cup\ \{space,\ comma,\ full\ stores \}$						
	of transmission} Where \cup denotes the union of two sets. How many bits of information will be required for the symbols? And how much time will be required to transmit					
	"Department of Electronic Sciences" at 9600 baud?					
	(A) 7-bits and 33 ms	(B) 6-bits and 40 ms				
	(C) 7-bits and 40 ms	(D) 8-bits and 30 ms				

98.	In terms of increasing speeds the ADCs can be listed as:						
	(A) Successive approximation, dual slope, flash						
	(B) Dual slope, successive approximation, flash						
	(C) Dual slope, flash, successive approximation(D) Flash, dual slope, successive approximation						
99.	99. Match the List I with List II and select the <i>correct</i> answer using the c given below it:						
		List I			List II		
	(a)	SRAM		(1)	Floating gate MOSFET		
	(b)	DRAM		(2)	Flip-Flop		
	(c)	Flash Men	nory	(3)	Magnetic		
	(d)	Hard Disk		(4)	MOSFET		
	Codes:						
		(a) (b) (d	(d)				
	(A)	(1) (2) (3)	3) (4)				
	(B)	(2) (4) (3) (1)				
	(C)	(2) (4) (1) (3)				
	(D)	(4) (1) (2)	2) (3)				
100.	100. Assertion (A):						
	Mu	ltiplexer car	n be used as a con	nfigurable	logic block.		
	Rea	ason (R):					
	Mu	ltiplexer act	s a Boolean proce	ssor.			
	(A)	Both (A) a	nd (R) are true as	nd (R) is	the correct explanation of (A)		
	(B) Both (A) and (R) are true but (R) is not the correct explanation of (A						
	(C) (A) is true but (R) is false						
	(D) (A) is false and (R) is true						

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ROUGH WORK